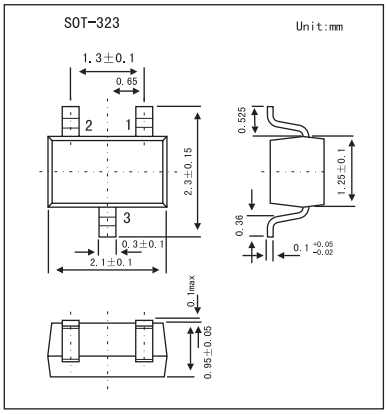
Silicon Schottky Diode

BAT68-04W,BAT68-05W,BAT68-06W



Features

- For mixer applications in VHF/UHF range
- For high-speed switching application

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	8	V
Forward current	I_F	130	mA
Total power dissipation $T_S \leqslant 92℃$	P_{tot}	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃
Junction - soldering point(Note 1)	R_{thJS}	⩽ 390	K/W

Note

1.For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)}$ = 10 μA	8			V
Reverse current	I_R	V_R = 1 V			0.1	μA
		V_R = 1 V, T_A = 60℃			1.2	
Forward voltage	V_F	I_F = 1 mA		318	340	mV
		I_F = 10 mA	340	390	500	
Diode capacitance	C_T	V_R = 0 , f = 1 MHz			1	pF
Differential forward resistance	R_F	I_F = 5 mA, f = 10 KHz			10	Ω

Marking

Type	BAT68-04W	BAT68-05W	BAT68-06W
Marking	84s	85s	86s